2SA1242

Rev.E May.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

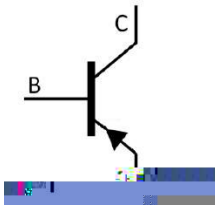
hFE

Excellent hFE linearity, low $V_{CE(sat)}$, high P_C.

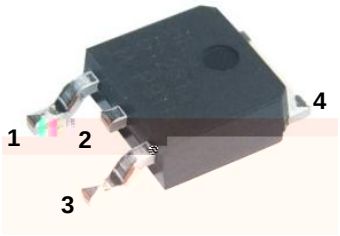
/ Applications

Strobe flash applications, medium power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

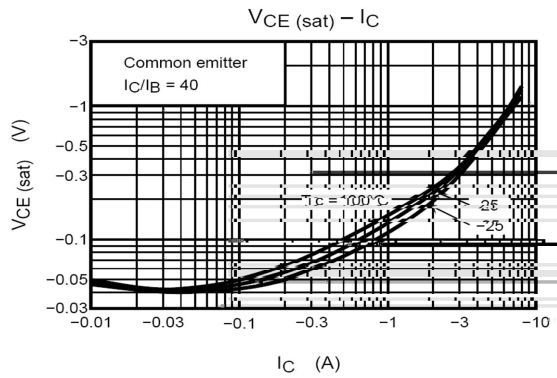
/ h_{FE} Classifications & Marking

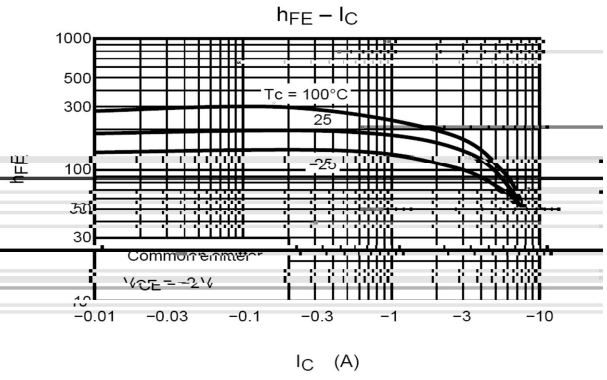
h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320

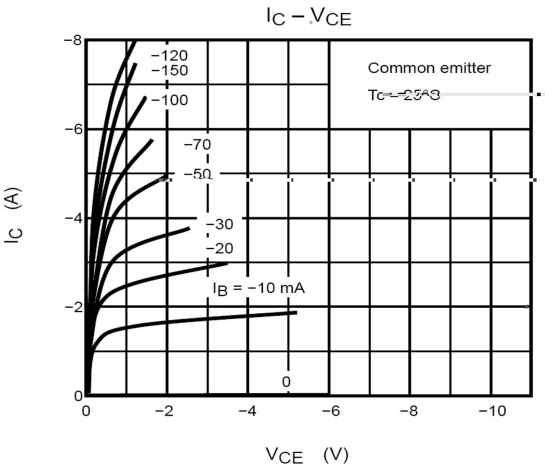
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-8.0	V
Collector Current - Continuous	I_C	-5.0	A
Base Current - Continuous	I_B	-0.5	A
Peak Collector Current - Continuous	I_{CM}	-8.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	P_C(Tc=25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

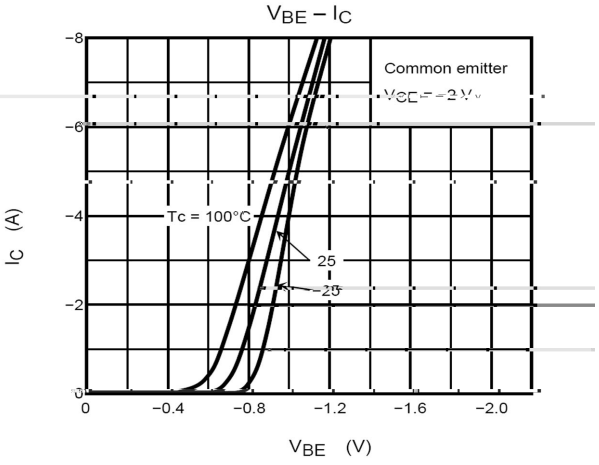
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-1.0mA I_C=0	-8.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-8.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-0.5A	100		320	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-4.0A	70			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-4.0A I_B=-0.1A			-1.0	V
Base to Emitter Voltage	V_{BE}	V_{CE}=-2.0V I_C				

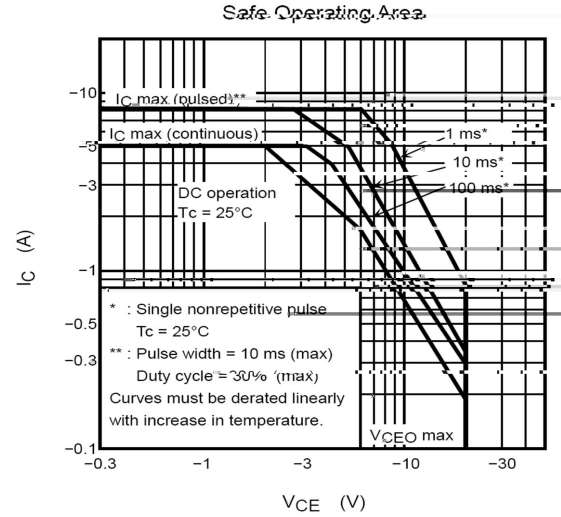
/ Electrical Characteristic Curve

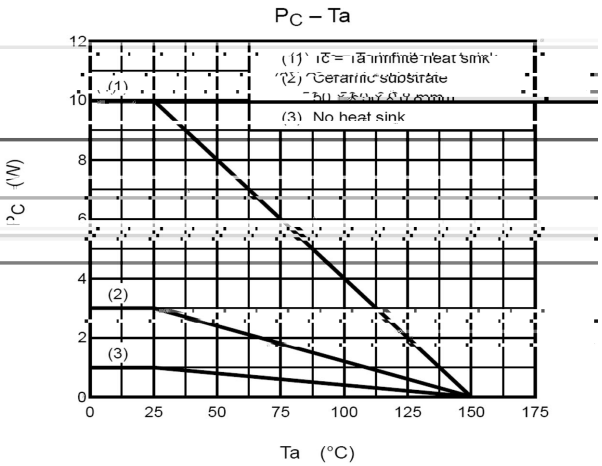




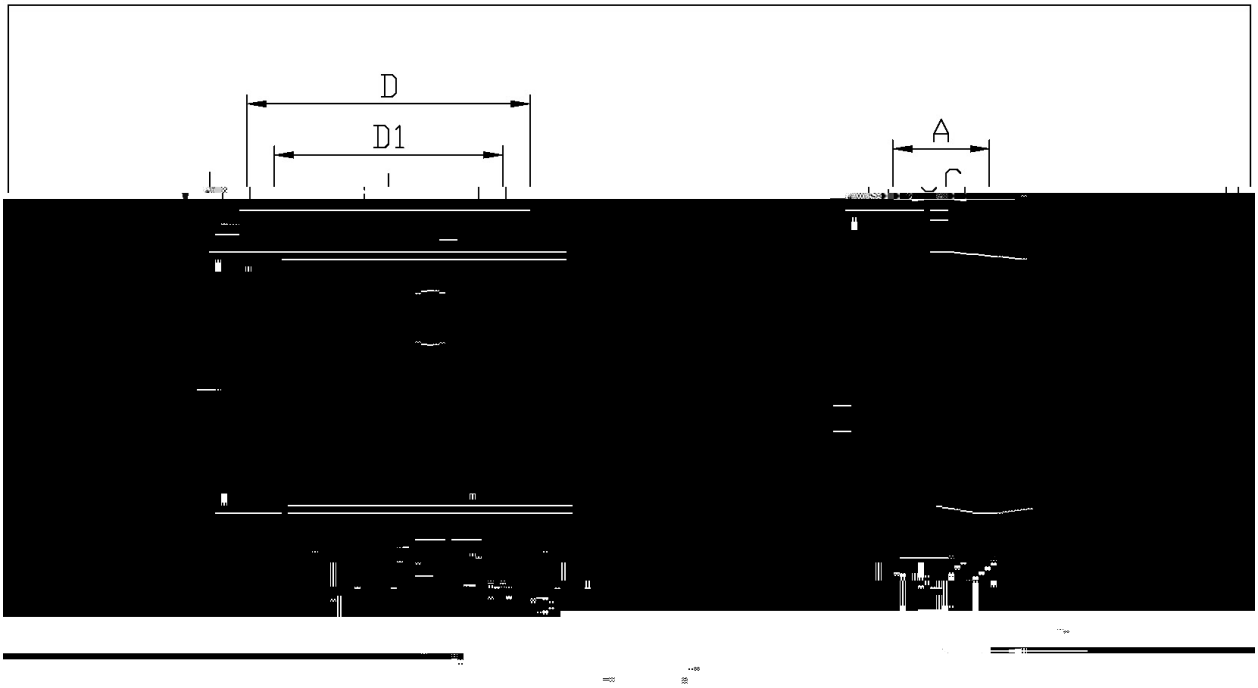


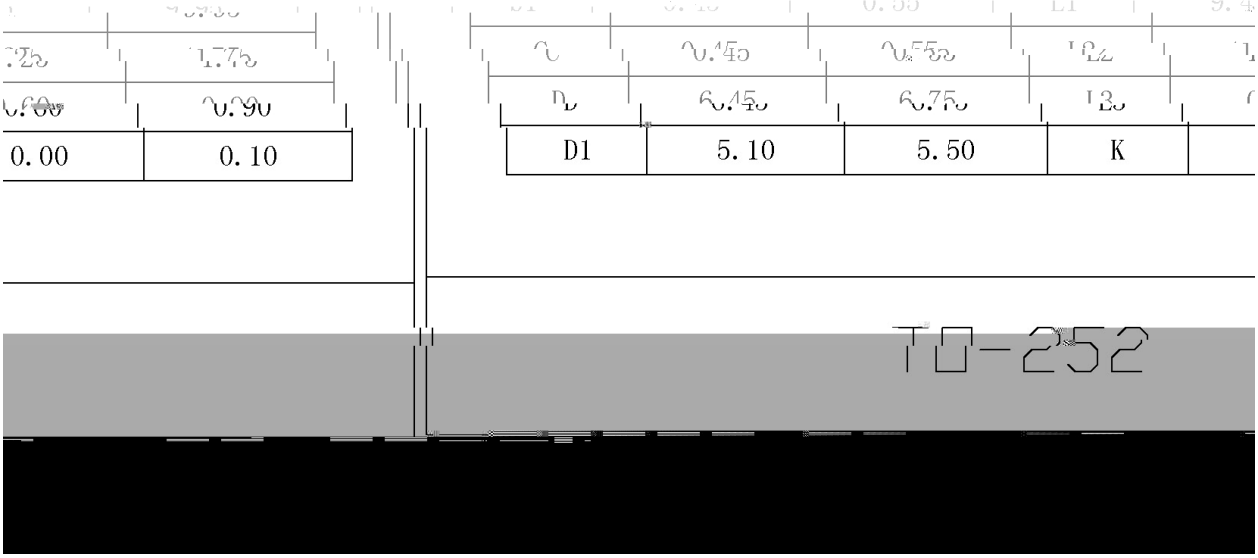


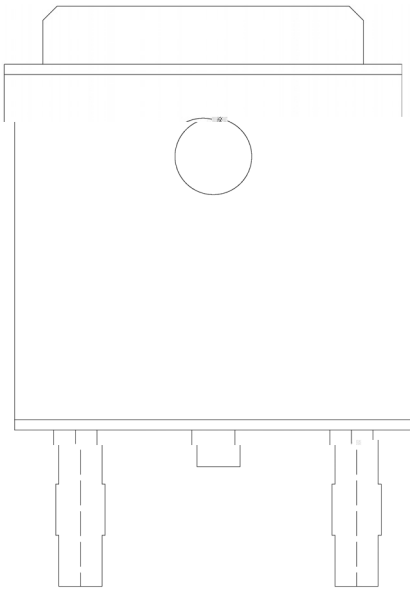




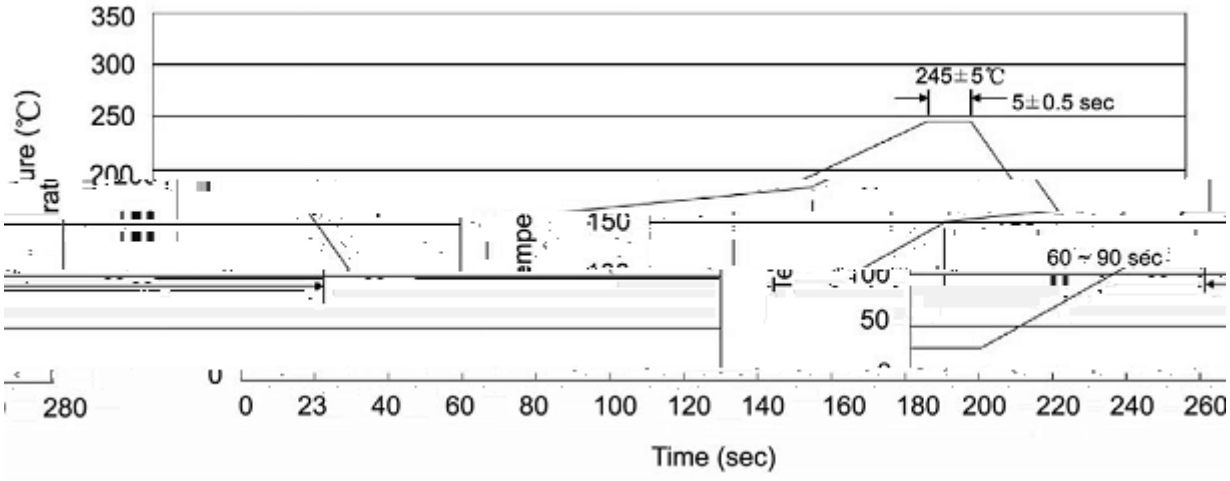
/ Package Dimensions







( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

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